

**Silicon Standard
Recovery Diode**
 $V_{RRM} = 200\text{ V} - 1000\text{ V}$
 $I_F = 150\text{ A}$
Features

- High Surge Capability
- Types up to 1000 V V_{RRM}

DO-8 Package

Maximum ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	150K(R)20A	150K(R)40A	150K(R)60A	150K(R)80A	150K(R)100A	Unit
Repetitive peak reverse voltage	V_{RRM}		200	400	600	800	1000	V
DC blocking voltage	V_{DC}		200	400	600	800	1000	V
Continuous forward current	I_F	$T_C \leq 110\text{ }^\circ\text{C}$	150	150	150	150	150	A
Surge non-repetitive forward current, Half Sine Wave	I_{FSM}	$T_C = 25\text{ }^\circ\text{C}$, $t_p = 8.3\text{ ms}$	3740	3740	3740	3740	3740	A
I_{2t} for fusing	I_{2t}	$t = 8.3\text{ms}$	58000	58000	58000	58000	58000	A^2sec
Operating temperature	T_j		-40 to 200	-40 to 200	-40 to 200	-40 to 200	-40 to 200	$^\circ\text{C}$
Storage temperature	T_{stg}		-40 to 200	-40 to 200	-40 to 200	-40 to 200	-40 to 200	$^\circ\text{C}$

Electrical characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	150K(R)20A	150K(R)40A	150K(R)60A	150K(R)80A	150K(R)100A	Unit
Diode forward voltage	V_F	$I_F = 150\text{ A}$, $T_j = 25\text{ }^\circ\text{C}$	1.33	1.33	1.33	1.33	1.33	V
Reverse current	I_R	$V_R = V_{RRM}$, $T_j = 175\text{ }^\circ\text{C}$	35	35	35	32	24	mA

Thermal characteristics

Thermal resistance, junction - case	$R_{\theta JC}$		0.25	0.25	0.25	0.25	0.25	$^\circ\text{C/W}$
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